PECVD-Turner05-LS SIN recipe-850A			PECVD1 LS SIN 850A Typical Film Properties
1. Chamber Clean (wet clean)	**2. Chamber (clean+coat)**	**3.LS SIN Deposition**	**Calibrated every 2-4 weeks**
WET CLEAN	**TURCLN**	**TURNER05**	**Check for the latest update on UCSB Nanofab WIKI**
Wipe clean upper chamber walls with DI	step1: Initial t=10", p=2x10-2 T=250C	step1: Initial t=10"	
Wipe off upper chamber walls with IPA	step2: N2 purge t=30" p=300mT	step2: N2 purge t=30"	
	step3: evacuate, base pressure=2x10-2, t=10"	step3: evacuate, t=10"	
	step4:loop	step4:loop	
	step5:gass stabilization, t=30"	step5: LSSIN gass stabilization, t=30"	**LS SIN 850A Typical Film properties**
	step6:etch chamber, t=30'	**step6:LSSIN deposition**	**Deposition rate~8.41nm/min**
	step7:evacuate, t=10"	**Time=10min30sec**	**Refractive index@632.8nm=1.966**
	step8:N2 purge	**Temperature=250°C**	**Stress=230MPa**
	step9:evacuate	**Pressure=900mT**	**HF etch rate=60nm/min**
	step10:loop	**Gass Flow:**	**Particle count (min=50, max=250)**
	step11:LSSIN gass stabilization	**SiH4=150sccm**	**Mostly small size particles (0.160-0.213)um**
Should be t~2min 16sec →	**step12:LSSIN deposition (200A coat) , t=2'29.7"**	**N2=59sccm**	**Uniformity within the wafer (99.2-99.5)%**
	step13:evacuate	**NH3=1.53**	
	step14:N2purge, t=30"		
	step15:end	**Power:**	
		RF1=22W	
		step7:evacuate, t=10"	
		step8:N2 purge t=30"	
		step9:evacuate t=10"	
		step10:loop